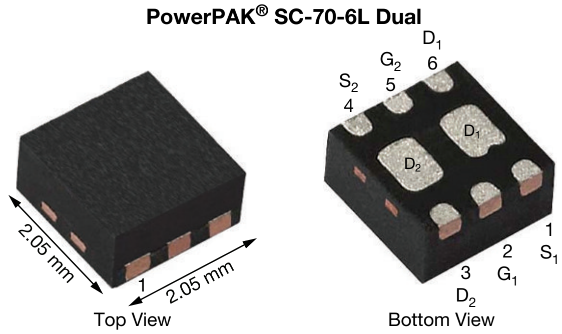
Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (TYP.)
-20	0.057 at V_{GS} = -4.5 V	-4.5 [a]	4.9 nC
	0.095 at V_{GS} = -2.5 V	-4.5 [a]	

PowerPAK® SC-70-6L Dual



Marking Code: DM

Ordering Information:
SiA907EDJT-T1-GE3 (Lead (Pb)-free and Halogen-free)
SiA907EDJT-T4-GE3 (Lead (Pb)-free and Halogen-free)

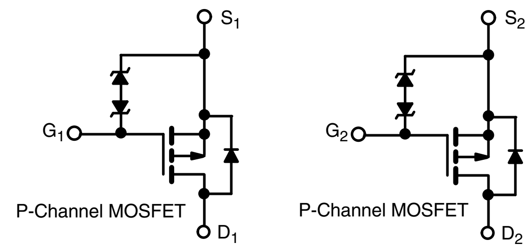
FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced Thin PowerPAK® SC-70 package
  - Small footprint area
  - Low on-resistance
- Typical ESD protection: 1500 V HBM
- High speed switching
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Charger Switch, Load Switch for Portable Devices
- Battery Management



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	-4.5 [a]	A
	T_C = 70 °C		-4.5 [a]	
	T_A = 25 °C		-4.5 [a, b, c]	
	T_A = 70 °C		-3.8 [b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	-15	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	-4.5 [a]	
	T_A = 25 °C		-1.6 [b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	7.8	W
	T_C = 70 °C		5	
	T_A = 25 °C		1.9 [b, c]	
	T_A = 70 °C		1.2 [b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C
Soldering Recommendations (Peak Temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient [b, f]	t ≤ 5 s	R_{thJA}	52	65	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16	

Notes

a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. See solder profile (www.vishay.com/doc?73257). The Thin PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 110 °C/W.

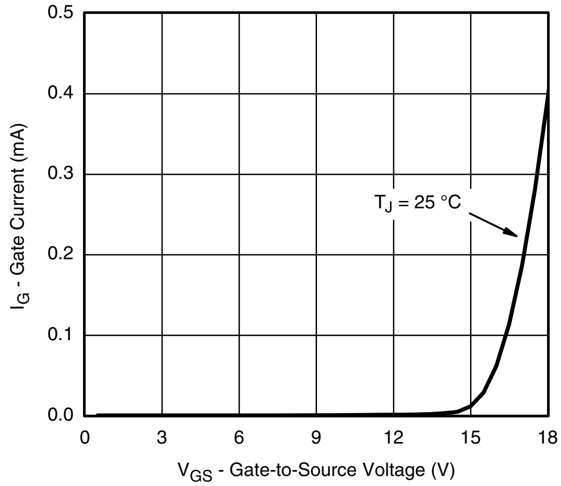
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 μA	-20	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = -250 μA	-	-14	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	2.5	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = -250 μA	-0.5	-	-1.4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 4.5 V	-	-	± 0.5	μA
		V_{DS} = 0 V, V_{GS} = ± 12 V	-	-	± 10	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -20 V, V_{GS} = 0 V	-	-	-1	
		V_{DS} = -20 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-10	
On-State Drain Current [a]	$I_{D(on)}$	$V_{DS} \leq$ -5 V, V_{GS} = -4.5 V	-15	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = -4.5 V, I_D = -3.6 A	-	0.047	0.057	Ω
		V_{GS} = -2.5 V, I_D = -1.5 A	-	0.075	0.095	
Forward Transconductance [a]	g_{fs}	V_{DS} = -10 V, I_D = -3.6 A	-	11	-	S
Dynamic [b]						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -10 V, I_D = -4.7 A	-	15	23	nC
		V_{DS} = -10 V, V_{GS} = -4.5 V, I_D = -4.7 A	-	7.1	11	
Gate-Source Charge	Q_{gs}		-	1.3	-	
Gate-Drain Charge	Q_{gd}		-	2.1	-	
Gate Resistance	R_g	f = 1 MHz	1.4	7	14	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 2.7 Ω $I_D \cong$ -3.7 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	13	25	ns
Rise Time	t_r		-	15	30	
Turn-Off Delay Time	$t_{d(off)}$		-	30	60	
Fall Time	t_f		-	10	15	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 2.7 Ω $I_D \cong$ -3.7 A, V_{GEN} = -10 V, R_g = 1 Ω	-	5	10	
Rise Time	t_r		-	10	20	
Turn-Off Delay Time	$t_{d(off)}$		-	30	60	
Fall Time	t_f		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	-4.5	A
Pulse Diode Forward Current	I_{SM}		-	-	-15	
Body Diode Voltage	V_{SD}	I_S = -3.7 A, V_{GS} = 0 V	-	-0.9	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = -3.7 A, dI/dt = 100 A/μs, T_J = 25 °C	-	15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	6	12	nC
Reverse Recovery Fall Time	t_a		-	8.5	-	ns
Reverse Recovery Rise Time	t_b		-	6.5	-	

Notes

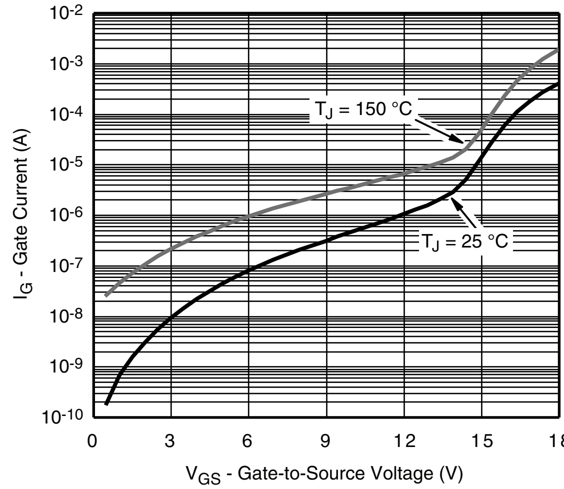
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

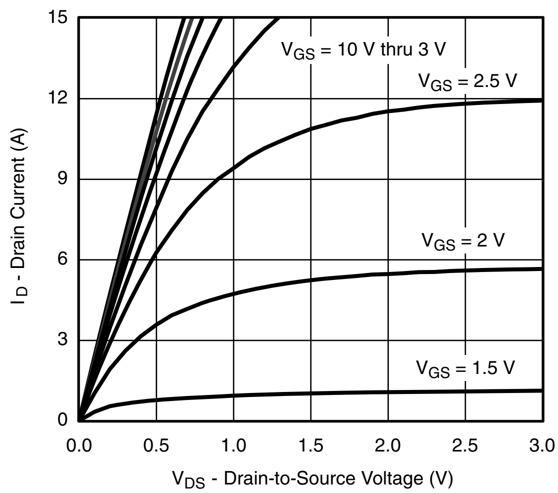
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



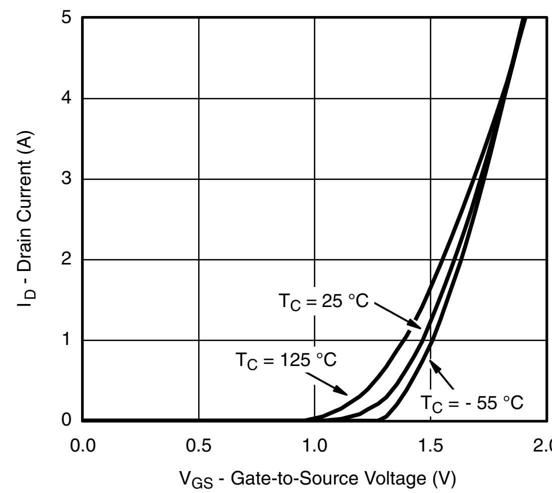
Gate Current vs. Gate-to-Source Voltage



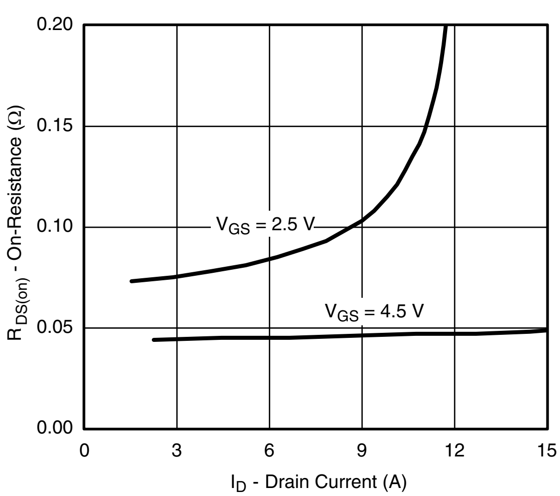
Gate Current vs. Gate-to-Source Voltage



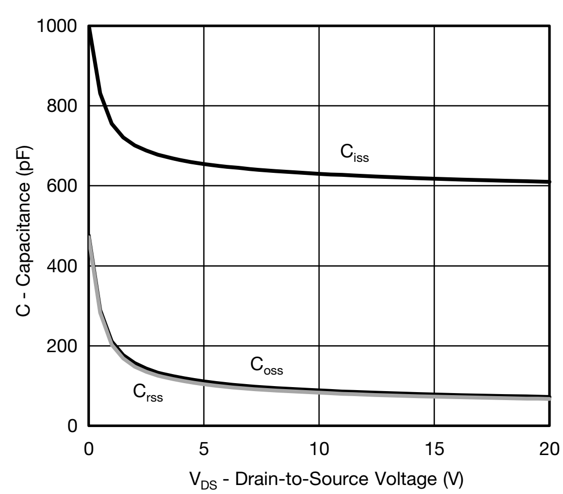
Output Characteristics



Transfer Characteristics

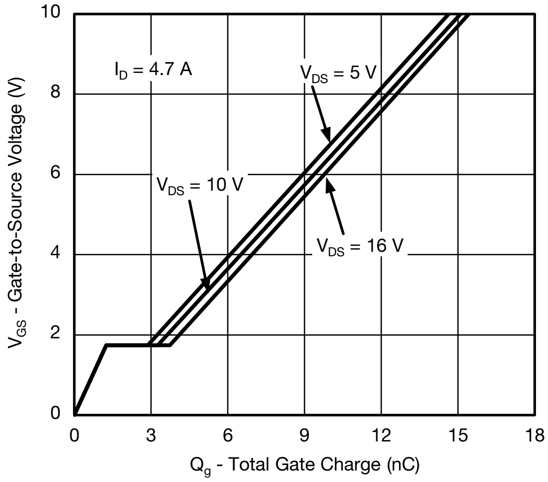


On-Resistance vs. Drain Current and Gate Voltage

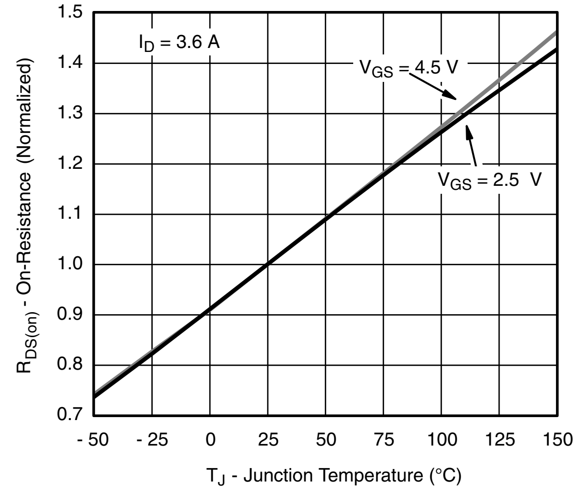


Capacitance

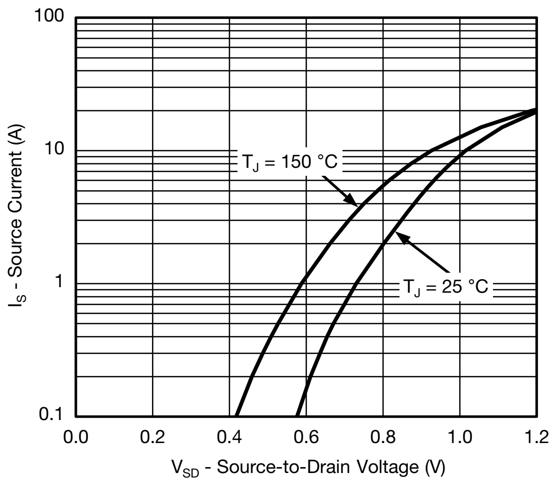
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



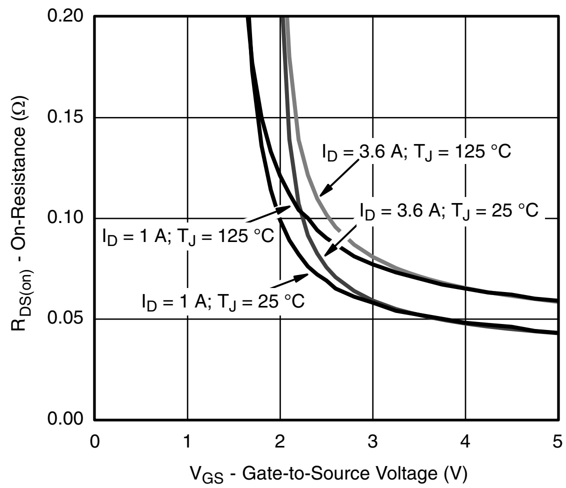
Gate Charge



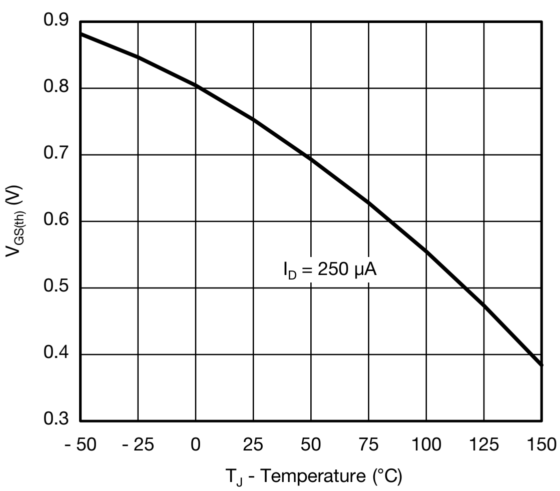
On-Resistance vs. Junction Temperature



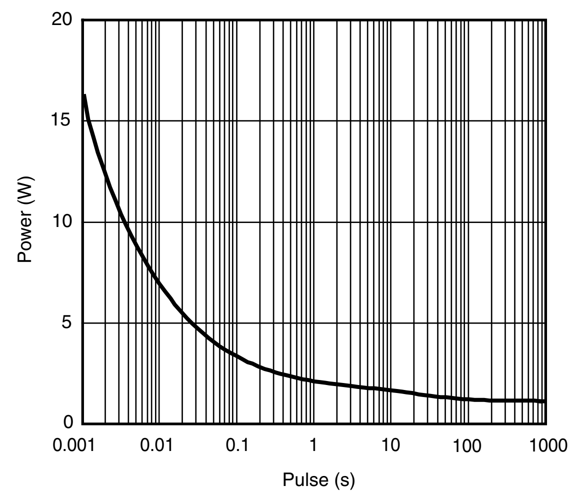
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

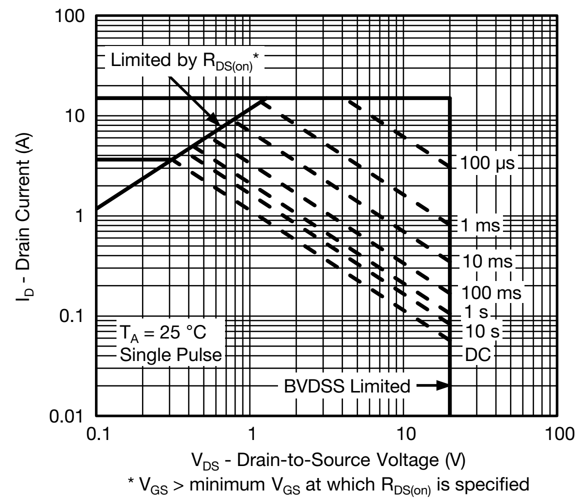


Threshold Voltage

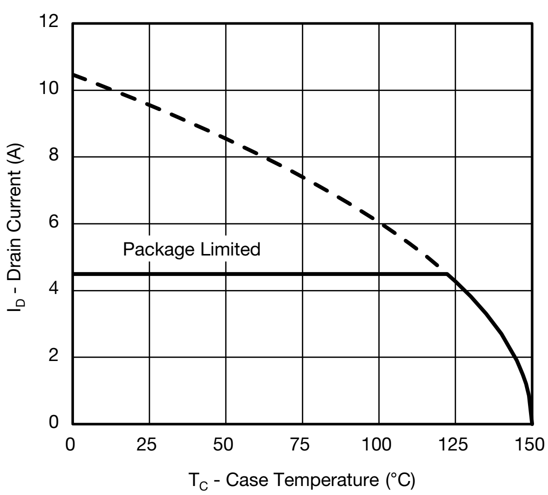


Single Pulse Power, Junction-to-Ambient

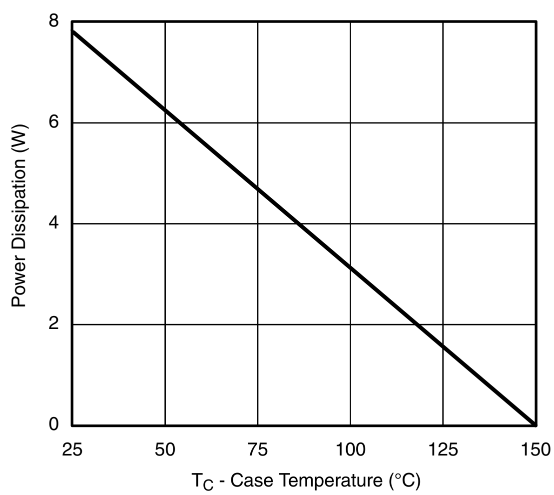
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient



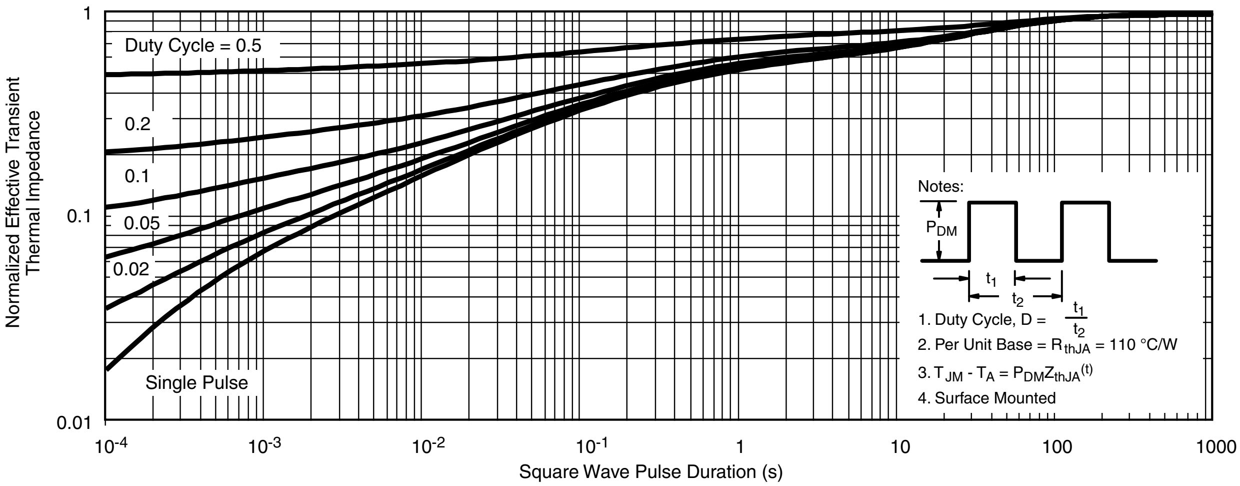
Current Derating*



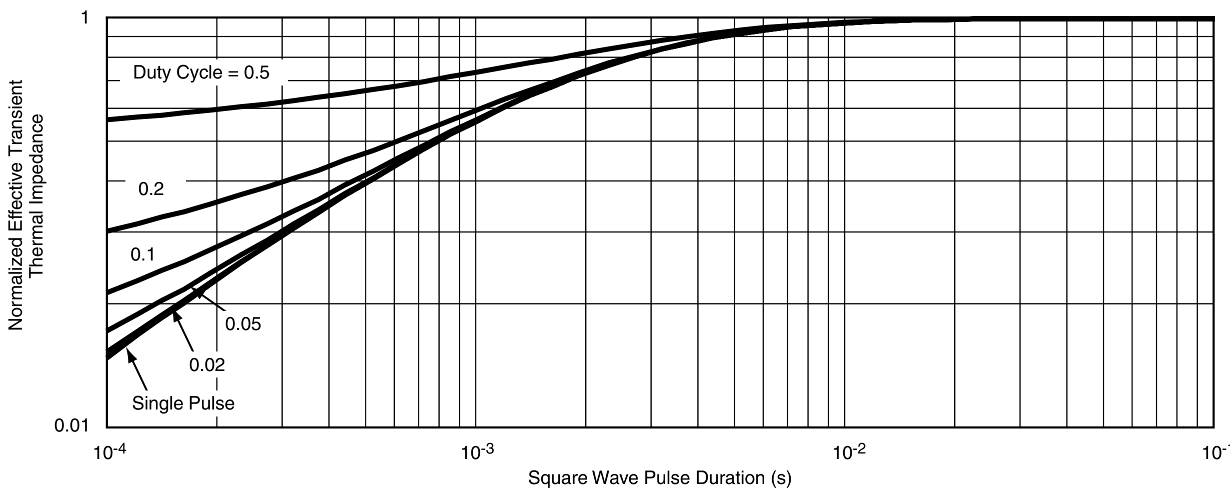
Power Derating

* The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



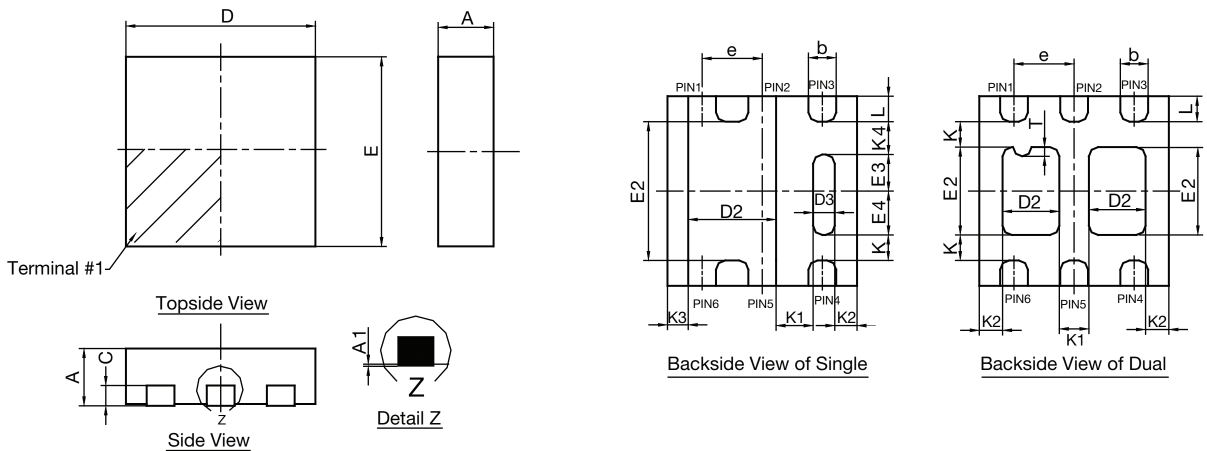
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67874.

Case Outline for PowerPAK® SC70T



DIM.	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D3	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E3	0.345	0.395	0.445	0.014	0.016	0.018						
E4	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP.			0.011 TYP.			0.275 TYP.			0.011 TYP.		
K1	0.400 TYP.			0.016 TYP.			0.320 TYP.			0.013 TYP.		
K2	0.240 TYP.			0.009 TYP.			0.252 TYP.			0.010 TYP.		
K3	0.225 TYP.			0.009 TYP.								
K4	0.355 TYP.			0.014 TYP.								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C12-0160-Rev. B, 05-Mar-12 DWG: 5994												

Notes

1. All dimensions are in millimeter. Millimeters will govern.
2. Package outline exculsive of mold flash and metal burr.
3. Package outline inclusive of plating

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